High Power RF Generation with Optically Activated Bulk GaAs Devices

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A. Kim, M. Weiner, R. Youmans, P. Herczfeld and A. Rosen. "High Power RF Generation with Optically Activated Bulk GaAs Devices." 1988 MTT-S International Microwave Symposium Digest 88.2 (1988 Vol. II [MWSYM]): 1071-1074.

Utilizing sections of charged transmission line cables and optically activated semiconductor switches, the direct generation of high power RF was demonstrated. A Nd:YAG laser was used to switch an array of GaAs semiconductors, biased at 2 KV DC, resulting in a peak RF output of 7.0 KW at VHF.

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